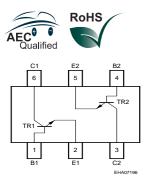


#### NPN Silicon RF Transistor\*

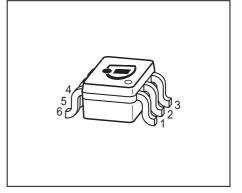
- For low noise, high-gain broadband amplifiers at collector currents from 0.5 mA to 12 mA
- $f_{\rm T}$  = 8 GHz, *F* = 0.9 dB at 900 MHz
- Two (galvanic) internal isolated Transistors in one package
- For orientation in reel see package information below
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101
- \* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BFS481	RFs	1=B	2=E	3=C	4=B	5=E	6=C	SOT363

<sup>1</sup>Pb-containing package may be available upon special request



# BFS481



#### **Maximum Ratings**

V <sub>CEO</sub>	10		
	12	V	
V <sub>CES</sub>	20		
V <sub>CBO</sub>	20		
V <sub>EBO</sub>	2		
I <sub>C</sub>	20	mA	
I <sub>B</sub>	2		
P <sub>tot</sub>	175	mW	
Ti	150	°C	
T <sub>A</sub>	-65 150		
T <sub>stq</sub>	-65 150		
	$ \begin{array}{c c} V_{CBO} \\ \hline V_{EBO} \\ \hline I_C \\ \hline I_B \\ \hline P_{tot} \\ \hline T_i \\ \hline T_A \\ \end{array} $	$V_{CBO}$ 20 $V_{EBO}$ 2 $I_C$ 20 $I_B$ 2 $P_{tot}$ 175 $T_i$ 150 $T_A$ -65 150	

# ParameterSymbolValueUnitJunction - soldering point2) $R_{thJS}$ $\leq$ 380K/W

## **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	12	-	-	V
<i>I</i> <sub>C</sub> = 1 mA, <i>I</i> <sub>B</sub> = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	100	μA
V <sub>CE</sub> = 20 V, V <sub>BE</sub> = 0					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0					
Emitter-base cutoff current	I <sub>EBO</sub>	-	-	1	μA
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain-	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, pulse measured					

 ${}^{1}T_{S}$  is measured on the collector lead at the soldering point to the pcb

<sup>2</sup>For calculation of  $R_{\rm thJA}$  please refer to Application Note Thermal Resistance



Parameter	Symbol		Values			
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Transition frequency	f <sub>T</sub>	6	8	-	GHz	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $f$ = 500 MHz						
Collector-base capacitance	C <sub>cb</sub>	-	0.23	0.4	pF	
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,						
emitter grounded						
Collector emitter capacitance	C <sub>ce</sub>	-	0.13	-		
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,						
base grounded						
Emitter-base capacitance	C <sub>eb</sub>	-	0.4	-		
$V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 ,						
collector grounded						
Noise figure	F				dB	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,						
<i>f</i> = 900 MHz		-	0.9	-		
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,						
f = 1.8 GHz		-	1.2	-		
Power gain, maximum stable <sup>1)</sup>	G <sub>ms</sub>	-	20	-	dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,						
<i>f</i> = 900 MHz						
Power gain, maximum available <sup>2)</sup>	G <sub>ma</sub>	-	15	-	dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,						
<i>f</i> = 1.8 GHz						
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω,						
<i>f</i> = 900 MHz		-	16	-		
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,						
<i>f</i> = 1.8 MHz		-	11	-		

# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

 ${}^{1}G_{\rm ms} = |S_{21} / S_{12}|$ 

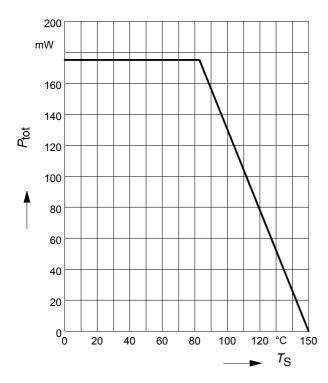
 ${}^{2}G_{\text{ma}} = |S_{21e} / S_{12e}| \ (k - (k^{2} - 1)^{1/2})$ 



**BFS481** 

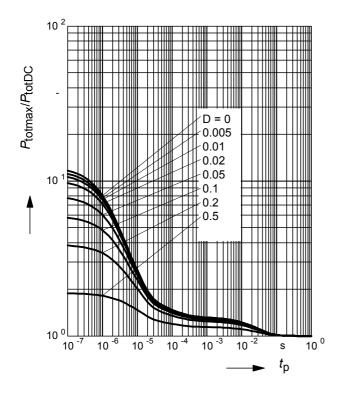
# Total power dissipation $P_{tot} = f(T_S)$

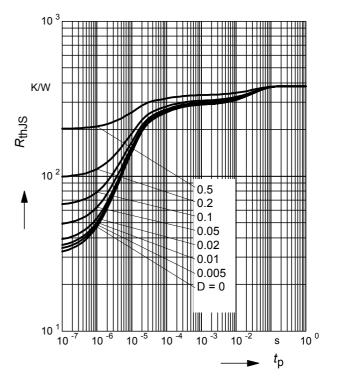
**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$ 



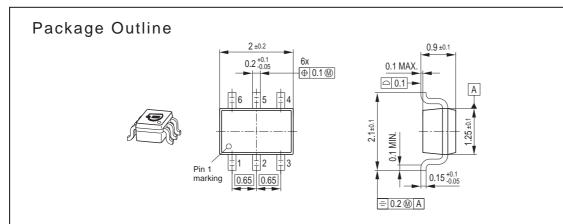
## Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$ 

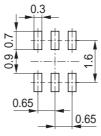






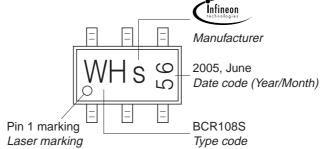


### Foot Print



## Marking Layout (Example)

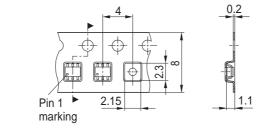
Small variations in positioning of Date code, Type code and Manufacture are possible.



#### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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